

AMENDMENTS TO THE SPECIFICATION

Paragraph beginning at page 1, line numbered 6:

The present invention relates to a dielectric ceramic, a manufacturing method thereof, and a multilayer ceramic capacitor formed of this dielectric ceramic. In particular, the present invention relates to improvements in the dielectric constant of a dielectric ceramic, in the temperature characteristics of the dielectric constant of a dielectric ceramic layer which is formed of the above dielectric ceramic and which forms a multilayer ceramic capacitor, and in the reliability thereof.

Paragraph beginning at page 3, line 1:

However, by firing in a neutral or a reducing atmosphere, in general, a ceramic composed, for example, of barium titanate is extremely reduced, and as a result, a problem may arise in that the ceramic ~~is semiconductorized~~ becomes semiconductive.

Paragraph beginning at page 6, line 2:

First, a method for manufacturing a dielectric ceramic, according to the present invention, comprises a first step of obtaining a reaction product composed of a barium titanate base composite oxide represented by the general formula $(\text{Ba}_{1-h-i-m}\text{Ca}_h\text{Sr}_i\text{Gd}_m)_k(\text{Ti}_{1-y-j-n}\text{Zr}_y\text{Hf}_j\text{Mg}_n)\text{O}_3$, in which $0.995 \leq k \leq 1.015$, $0 \leq h \leq 0.03$, $0 \leq i \leq 0.03$, $0.015 \leq m \leq 0.035$, $0 \leq y < 0.05$, $0 \leq j < 0.05$, $0 \leq (y+j) < 0.05$, and $0.015 \leq n \leq 0.035$ ~~hold~~, Ba ~~is being~~ partly replaced with Gd, and Ti ~~is being~~ partly replaced with Mg.

Paragraph beginning at page 10, line 18:

In addition, even when being fired in a neutral or a reducing atmosphere, the dielectric ceramic of the present invention is not rendered semiconductive ~~semiconductorized~~ and may have a high specific resistance. Accordingly, when a multilayer ceramic capacitor is formed using this dielectric ceramic, a base metal can be used as a conductive component contained in interior electrodes without causing any problems, and as a result, cost of the multilayer ceramic capacitor can be reduced.

Paragraph beginning at page 26, line 1:

In addition, ~~in~~ from a static capacitance-temperature curve in the range of from -25 to 85°C obtained in an AC electric field of 25 V_{rms}/mm at 1 kHz, ~~at the~~ temperature was ~~measured~~ identified at which a peak capacitance was obtained. In this case, when the AC voltage is increased, an apparent capacitance in a temperature range in which the ferroelectricity is observed is increased, and as a result, the temperature of the peak capacitance is shifted to a lower temperature side. Accordingly, in this measurement, an electric field of 25 V_{rms}/mm was used which was sufficiently low so that the peak temperature was not shifted.

Paragraph beginning at page 31, line 12:

~~In~~ samples 1-105 and 1-106, ~~which~~ are outside the scope of the present invention, as shown in Table 2, since the y value and the j value are each 0.05 or more, and ~~in~~ sample 1-107 ~~which~~ is outside the scope of the present invention, the (y + j) value

is 0.05 or more. As a result, according to samples 1-105, 1-106, and 1-107, as shown in Table 4, the average lifetime under high-temperature loading conditions is short.

Paragraph beginning at page 32, line 21:

In sample 1-114 which is outside the scope of the present invention, since Mb is not contained as shown in Table 2, the sintered body is made semiconductive~~orized~~ as shown in Table 4. In addition, in sample 1-115 which is outside the scope of the present invention, since more than 1.0 mole of Mb is contained as shown in Table 2, the relative dielectric constant is less than 9,000 as shown in Table 4.